



Notes for building:

- Q1, Q2, Q3 are all PNP germanium transistors in the original
- If using NPN, use +9V in place of -9V and reverse the polarity of the 25uF electrolytic
- Level pot is A500K
- Attack pot is originally B50K but B10K may result in less bunching
- If 180KΩ resistors are unavailable, use 330KΩ and 390KΩ in parallel to make 180KΩ